

ABSTRACT OF THE DISCLOSURE

According to this invention, residues generated after selectively removing a low-dielectric-constant film such as SiOC can be effectively removed without damage on an insulating film or metal film. Specifically, residues
5 126 and 128 generated after forming an interconnect trench in an SiOC film 116 are removed using a fluoride-free weak alkaline amine stripper. After the removing step, the wafer is rinsed with isopropyl alcohol and then dried without drying with pure water.